

ABSTRACT

A light emitting device having practical light emission characteristics is obtained without epitaxial growth.

A quantum dot-dispersed light emitting device of the invention includes a substrate 11, an electron injection electrode 12, a hole injection electrode 14, and an inorganic light emitting layer 13 disposed so as to be in contact with both the electrodes. The inorganic light emitting layer 13 contains an ambipolar inorganic semiconductor material and nanocrystals 15 dispersed as luminescent centers in the ambipolar inorganic semiconductor material and is configured so as to be capable of light emission without having, at the interface with the electron injection electrode and/or the hole injection electrode, epitaxial relation therewith.